



STPS5L40-C2

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	5 A
V_{RRM}	40 V
T_j (max)	150°C
V_F (max)	0.44 V

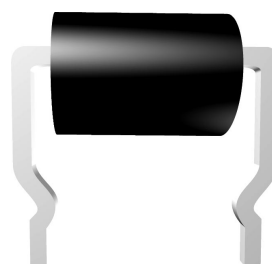
FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP FOR HIGHER EFFICIENCY.
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Axial Power Schottky rectifier suited for Switch Mode Power Supplies and high frequency inverters.

Packaged in DO-201AD, this device is intended for use in low voltage output for small battery chargers & consumer SMPS such as DVD and Set-Top-Box.



DO-201AD
STPS5L40-C2

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		40	V
$I_{F(RMS)}$	RMS forward current		15	A
$I_{F(AV)}$	Average forward current	$T_I = 100^\circ\text{C} \quad \delta = 0.5$	5	A
I_{FSM}	Surge non repetitive forward current	Half wave, single phase $t_p = 10 \text{ ms}$	150	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1\mu\text{s} \quad T_j = 25^\circ\text{C}$	2700	W
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise of reverse voltage (rated V_R , $T_j = 25^\circ\text{C}$)		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

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THERMAL PARAMETERS

Symbol	Parameter		Value	Unit
$R_{th(j-a)}$	Junction to ambient		75	°C/W
$R_{th(j-l)}$	Junction to leads	Lead length = 10 mm	15	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			0.2	mA
		$T_j = 100^\circ\text{C}$			8	25	
		$T_j = 125^\circ\text{C}$			25	75	
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 5\text{ A}$		0.44	0.50	V
		$T_j = 100^\circ\text{C}$			0.40	0.46	
		$T_j = 125^\circ\text{C}$			0.38	0.44	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

$$P = 0.34 \times I_{F(AV)} + 0.028 \times I_{F(RMS)}^2$$

Fig. 1: Conduction losses versus average current.

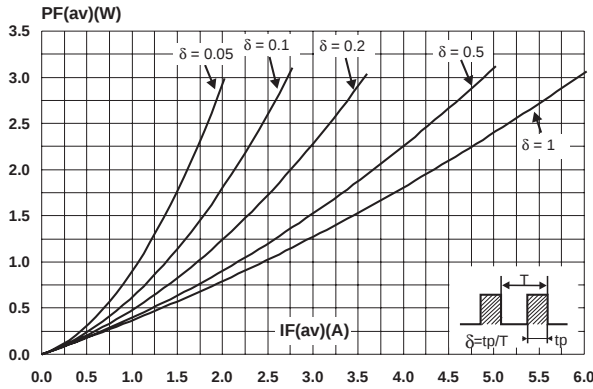


Fig. 3: Normalized avalanche power derating versus pulse duration.

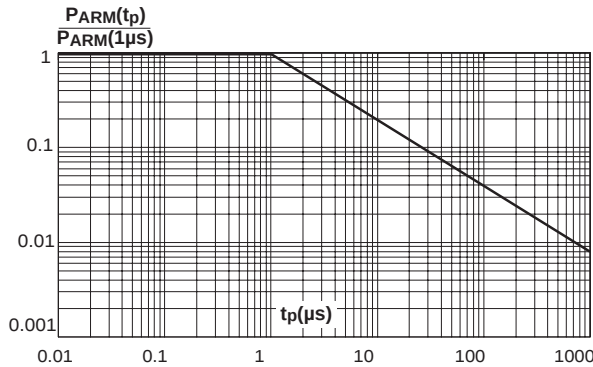


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

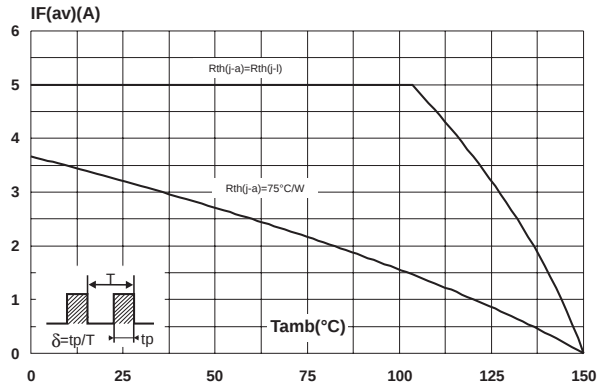


Fig. 4: Normalized avalanche power derating versus junction temperature.

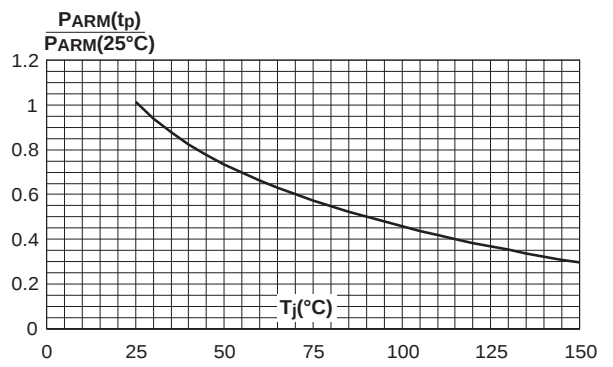


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

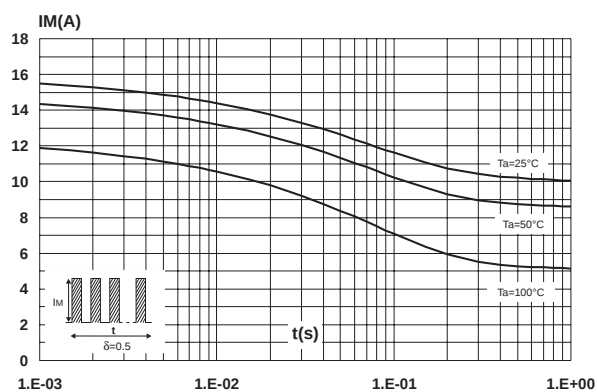


Fig. 6: Relative variation of thermal impedance junction to ambient versus pulse duration.

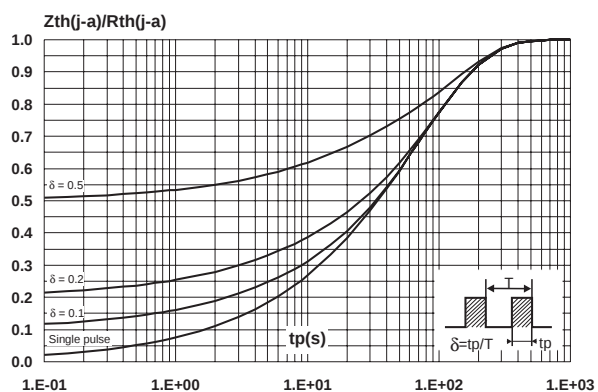


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

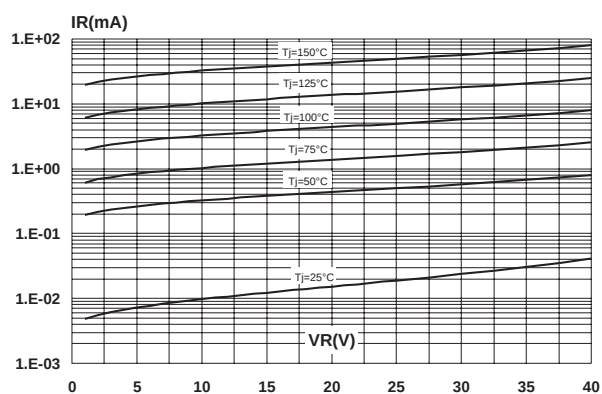


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

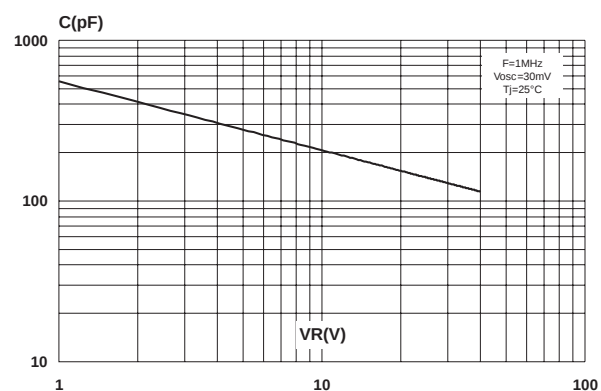


Fig. 9-1: Forward voltage drop versus forward current (low level).

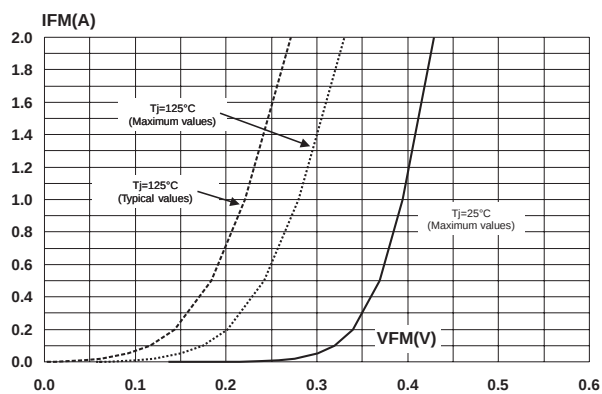
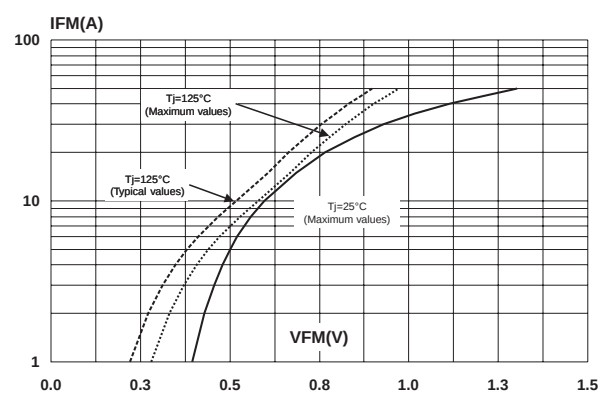


Fig. 9-2: Forward voltage drop versus forward current (high level).



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Fig. 10: Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed board FR4, Cu = 35µm).

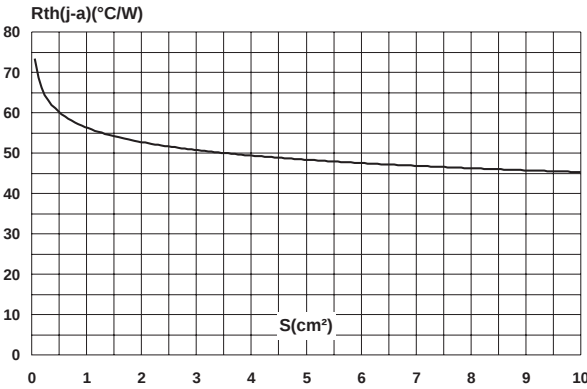
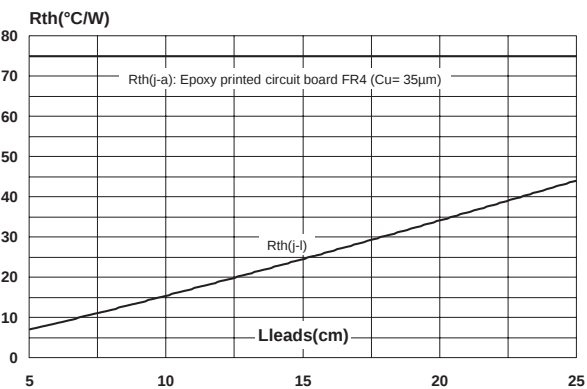
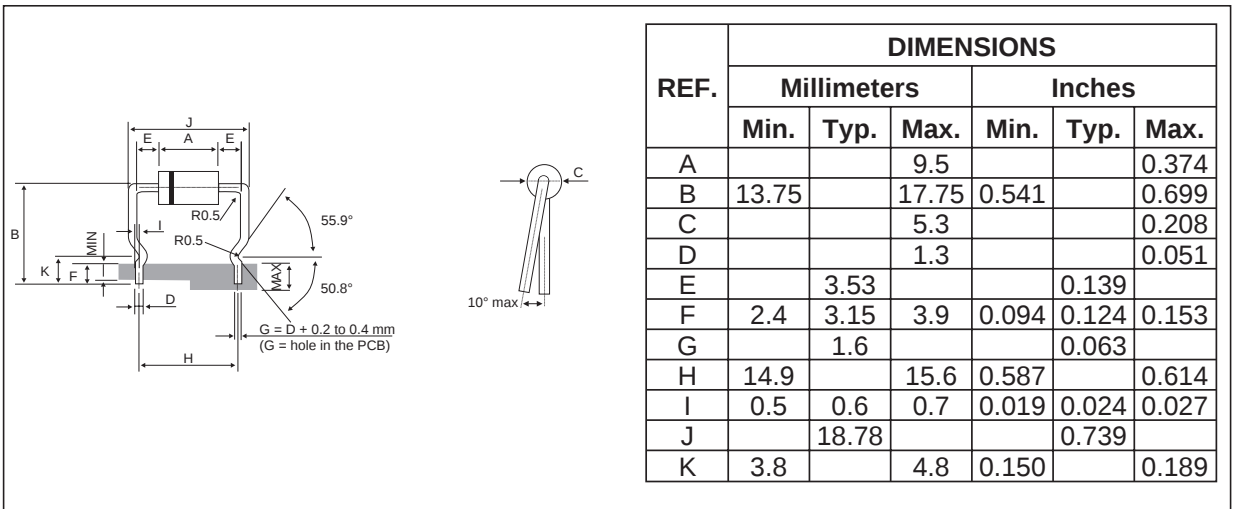


Fig. 11: Thermal resistances versus leads length.



PACKAGE MECHANICAL DATA

DO-201AD plastic



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS5L40-C2	STPS5L40	DO-201AD	1.12g	500	Ammopack

- WHITE BAND INDICATES CATHODE
- EPOXY MEETS UL94,V0

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